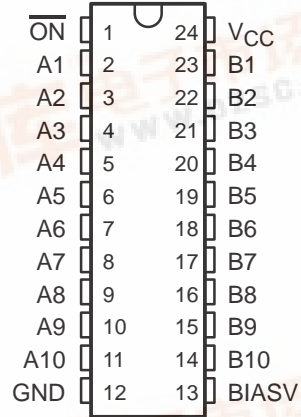


SN74CBTK6800 10-BIT FET BUS SWITCH WITH PRECHARGED OUTPUTS AND ACTIVE-CLAMP UNDERSHOOT-PROTECTION CIRCUIT

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- **5-Ω Switch Connection Between Two Ports**
- **TTL-Compatible Input Levels**
- **Power Off Disables Outputs, Permitting Live Insertion**
- **Outputs Are Precharged by Bias Voltage to Minimize Signal Distortion During Live Insertion**
- **Active-Clamp Undershoot-Protection Circuit on the I/Os Clamps Undershoots Down to -2 V**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Protection Exceeds JESD 22**
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- **Package Options Include Plastic Shrink Small-Outline (DBQ), Thin Very Small-Outline (DGV), Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages**

DBQ, DGV, DW, OR PW PACKAGE
(TOP VIEW)



description

The SN74CBTK6800 device provides ten bits of high-speed TTL-compatible bus switching. The low on-state resistance of the switch allows bidirectional connections to be made while adding near-zero propagation delay. The device also precharges the B port to a user-selectable bias voltage (BIASV) to minimize live-insertion noise.

The A and B ports have an active-clamp undershoot-protection circuit. When there is an undershoot, the active-clamp circuit is enabled and current from V_{CC} is supplied to clamp the output, preventing the pass transistor from turning on.

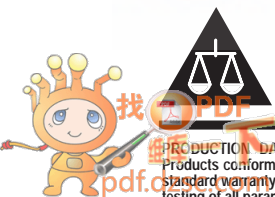
The SN74CBTK6800 is organized as one 10-bit switch with a single enable ($\overline{\text{ON}}$) input. When $\overline{\text{ON}}$ is low, the switch is on and port A is connected to port B. When $\overline{\text{ON}}$ is high, the switch between port A and port B is open. When $\overline{\text{ON}}$ is high or V_{CC} is 0 V, B port is precharged to BIASV through the equivalent of a 10-kΩ resistor.

The SN74CBTK6800 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

INPUT $\overline{\text{ON}}$	FUNCTION
L	A port = B port
H	A port = Z B port = BIASV

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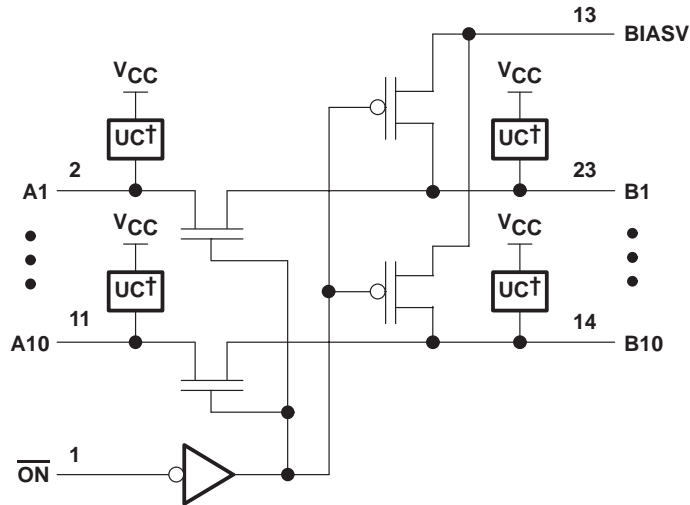


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10-BIT FET BUS SWITCH WITH PRECHARGED OUTPUTS AND ACTIVE-CLAMP UNDERSHOOT-PROTECTION CIRCUIT

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logic diagram (positive logic)



† Undershoot clamp

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}	-0.5 V to 7 V
Bias voltage range, BIASV	-0.5 V to 7 V
Input voltage range, V_I (see Note 1)	-0.5 V to 7 V
Continuous channel current	128 mA
Input clamp current, I_{IK} ($V_I < 0$)	-50 mA
Package thermal impedance, θ_{JA} (see Note 2):		
DBQ package	61°C/W
DGV package	86°C/W
DW package	46°C/W
PW package	88°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	4	5.5	V
BIASV	Supply voltage	1.3	V_{CC}	V
V_{IH}	High-level control input voltage	2		V
V_{IL}	Low-level control input voltage		0.8	V
T_A	Operating free-air temperature	-40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IK}		$V_{CC} = 4.5\text{ V}$, $I_I = -18\text{ mA}$				-1.2	V
V_{IKU}		$V_{CC} = 5.5\text{ V}$, $0\text{ mA} \geq I_I \geq -50\text{ mA}$, $\overline{OE} = 5.5\text{ V}$				-2	V
I_I		$V_{CC} = 5.5\text{ V}$, $V_I = 5.5\text{ V}$ or GND				± 5	μA
I_{off}		$V_{CC} = 0$, V_I or $V_O = 0$ to 5.5 V , $\text{BIASV} = \text{Open}$				20	μA
I_O		$V_{CC} = 4.5\text{ V}$, $V_O = 0$, $\text{BIASV} = 2.4\text{ V}$		0.25			mA
I_{CC}		$V_{CC} = 5.5\text{ V}$, $V_I = V_{CC}$ or GND, $I_O = 0$				20	μA
ΔI_{CC}^\ddagger	Control inputs	$V_{CC} = 5.5\text{ V}$, One input at 3.4 V , Other inputs at V_{CC} or GND				2.5	mA
C_i	Control inputs	$V_I = 3\text{ V}$ or 0			3		pF
$C_o(\text{OFF})$		$V_O = 3\text{ V}$ or 0, Switch off			8.5		pF
r_{on}^\S		$V_{CC} = 4\text{ V}$, TYP at $V_{CC} = 4\text{ V}$	$V_I = 2.4\text{ V}$, $I_I = 15\text{ mA}$		11	20	Ω
			$V_I = 0$, $I_I = 64\text{ mA}$		3	7	
		$V_{CC} = 4.5\text{ V}$	$I_I = 30\text{ mA}$		3	7	
			$V_I = 2.4\text{ V}$, $I_I = 15\text{ mA}$		6	15	

† All typical values are at $V_{CC} = 5\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

‡ This is the increase in supply current for each input that is at the specified TTL-voltage level rather than V_{CC} or GND.

§ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	TEST CONDITIONS	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 4\text{ V}$		$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$		UNIT
				MIN	MAX	MIN	MAX	
t_{pd}^\parallel		A or B	B or A	0.35		0.25		ns
t_{PZH}	$\text{BIASV} = \text{GND}$	ON	A or B	6		2	5.1	ns
t_{PZL}	$\text{BIASV} = 3\text{ V}$			6		2	5.6	
t_{PHZ}	$\text{BIASV} = \text{GND}$	$\overline{\text{ON}}$	A or B	5.5		1	5	ns
t_{PLZ}	$\text{BIASV} = 3\text{ V}$			5.5		2	5.9	

¶ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

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undershoot characteristics

PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OUTU}	See Figures 1 and 2, and Table 1	2	$V_{OH}-0.3$		V

† All typical values are at $V_{CC} = 5\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

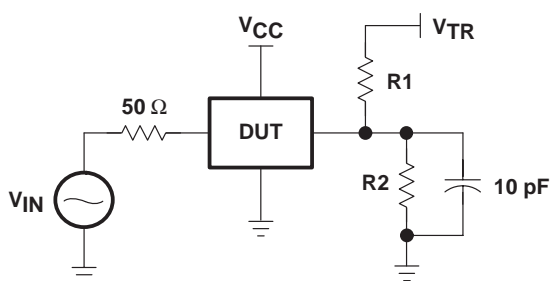


Figure 1. Device Test Setup

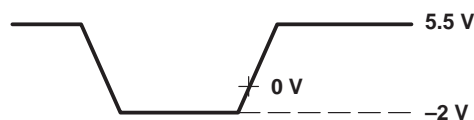


Figure 2. Transient Input Voltage Waveform

Table 1. Device Test Conditions

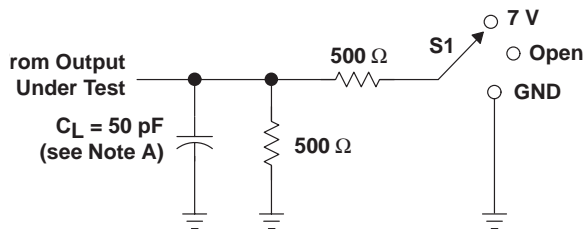
PARAMETER	VALUE	UNIT
B port under test‡	See Figure 1	
V_{IN}	See Figure 2	V
t_w	20	ns
t_r	2	ns
t_f	2	ns
$R1 = R2$	100	k Ω
V_{TR}	11	V
V_{CC}	5.5	V
BIASV	Open	

‡ Other B-port outputs are open.

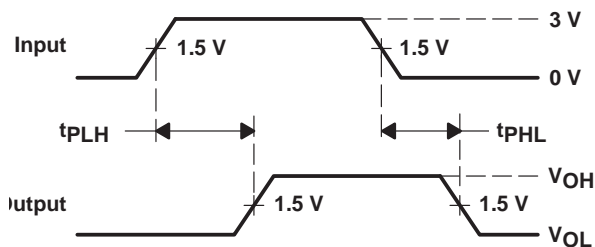
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PARAMETER MEASUREMENT INFORMATION

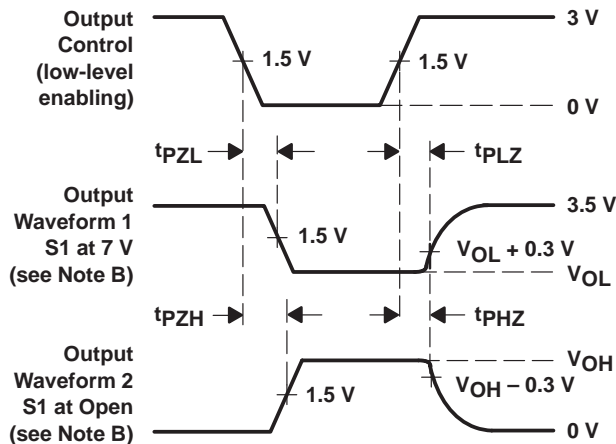


LOAD CIRCUIT



**VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES**

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open



**VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES**

- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

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